

WEST**Freeform Search**

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US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
EPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Term:

Display: 50 Documents in Display Format: - Starting with Number 1

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Search HistoryDATE: Thursday, May 23, 2002 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR YES; OP OR</i>			
<u>L12</u>	l3 and l11	11	<u>L12</u>
<u>L11</u>	l2 near l8	51	<u>L11</u>
<u>L10</u>	l4 and l8	106	<u>L10</u>
<u>L9</u>	l4 same l8	8	<u>L9</u>
<u>L8</u>	carboni\$4	56395	<u>L8</u>
<u>L7</u>	l4 same l5	754	<u>L7</u>
<u>L6</u>	l4 same l5	754	<u>L6</u>
<u>L5</u>	carbon\$5	1244473	<u>L5</u>
<u>L4</u>	l2 same l3	34669	<u>L4</u>
<u>L3</u>	dop\$4	234222	<u>L3</u>
<u>L2</u>	L1 adj4 (layer or film)	188814	<u>L2</u>
<u>L1</u>	silicon or si	1336732	<u>L1</u>

END OF SEARCH HISTORY

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L11: Entry 44 of 51

File: DWPI

Jul 1, 1991

DERWENT-ACC-NO: 1991-234547

DERWENT-WEEK: 199132

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TITLE: Growing single-crystal silicon carbide layer on silicon wafer - by depositing silicon layer on carbonised wafer surface, and heating in hydrocarbon atmos. NoAbstract Dwg 1,2/2

PATENT-ASSIGNEE: FUJITSU LTD (FUIT)

PRIORITY-DATA: 1989JP-0292903 (November 10, 1989)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 03153023 A	July 1, 1991		000	

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
JP03153023A	November 10, 1989	1989JP-0292903	

INT-CL (IPC): H01L 21/20

DERWENT-CLASS: L03 U11

CPI-CODES: L04-A; L04-A01; L04-C16;

EPI-CODES: U11-C01A9; U11-C01J4; U11-C03J7;

57.6 208US PTO
U-S PATENT

J: